

General Description

The WSR80N10D use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable to use in.

Features

Low RDS(on) & FOM Extremely low switching loss
Excellent stability and uniformity or Invertors

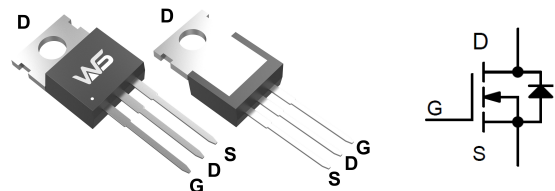
Product Summary

BVDSS	RDSON	ID
100V	9mΩ	60A

Applications

Consumer electronic power supply Motor control
Synchronous-rectification Isolated DC
Synchronous-rectification applications

TO-220AB Pin Configuration



Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V _{DS}	Drain source voltage	100	V
V _{GS}	Gate source voltage	±20	V
I _D	Continuous drain current ¹⁾	TC=25 °C 60	A
I _{D, pulse}	Pulsed drain current ²⁾	TC=25 °C 180	A
P _D	Power dissipation ³⁾	TC=25 °C 107	W
E _{AS}	Single pulsed avalanche energy ⁴⁾	183.8	mJ
T _{stg} , T _j	Operation and storage temperature	-55 to 150	°C
R _{θJC}	Thermal resistance, junction-case	1.17	°C/W
R _{θJA}	Thermal resistance, junction-ambient ⁴⁾	62	°C/W

Electrical Characteristics at $T_j=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-source breakdown voltage	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	100	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$	1.5	-	2.5	V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$	-	9	10.0	m Ω
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS}=4.5\text{ V}$, $I_D=12\text{ A}$	-	12	14.0	m Ω
I_{GSS}	Gate-source leakage current	$V_{GS}=20\text{ V}$	-	-	100	nA
		$V_{GS}=-20\text{ V}$	-	-	-100	
I_{DSS}	Drain-source leakage current	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$	-	-	1	μA
R_G	Gate resistance	$f=1\text{ MHz}$, Open drain	-	5.5	-	Ω
C_{iss}	Input capacitance	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$ $V_{GS}=10\text{ V}$,	-	1999	-	pF
C_{oss}	Output capacitance		-	322	-	pF
C_{rss}	Reverse transfer capacitance		-	7.1	-	pF
$t_{d(on)}$	Turn-on delay time		-	22.1	-	ns
t_r	Rise time		$V_{DS}=50\text{ V}$,	-	5.2	-
$t_{d(off)}$	Turn-off delay time	$R_G=2\text{ }\Omega$,	-	44	-	ns
t_f	Fall time	$I_D=25\text{ A}$ $I_D=25\text{ A}$, $V_{DS}=50\text{ V}$, $V_{GS}=10\text{ V}$ $V_{GS}<V_{th}$	-	8.4	-	ns
Q_g	Total gate charge		-	28.9	-	nC
Q_{gs}	Gate-source charge		-	6	-	nC
Q_{gd}	Gate-drain charge		-	6.8	-	nC
$V_{plateau}$	Gate plateau voltage		-	3.7	-	V
I_S	Diode forward current	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$	-	-	60	A
I_{SP}	Pulsed source current		-	-	180	A
V_{SD}	Diode forward voltage		-	-	1.3	V
t_{rr}	Reverse recovery time	$I_S=25\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$	-	102.9	-	ns
Q_{rr}	Reverse recovery charge		-	379	-	nC
I_{rrm}	Peak reverse recovery current		-	6.4	-	A

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=50\text{ V}$, $R_G=25\text{ }\Omega$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.
- 5) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.

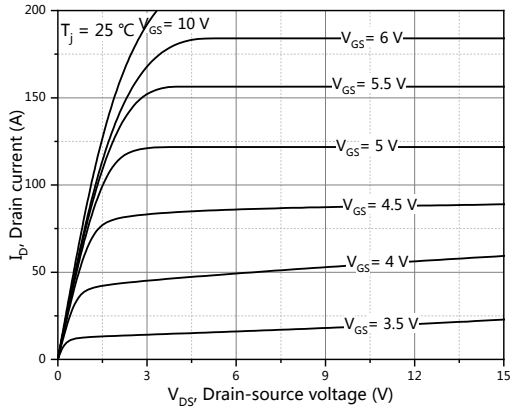


Figure 1, Typ. output characteristics

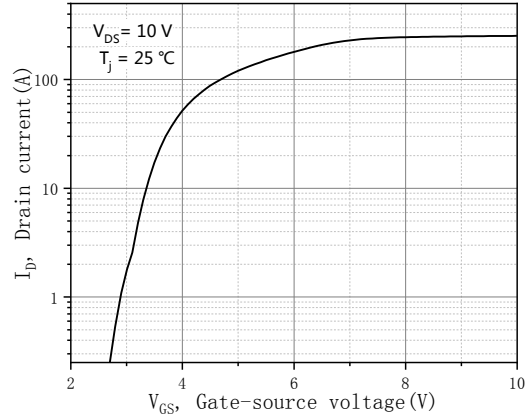


Figure 2, Typ. transfer characteristics

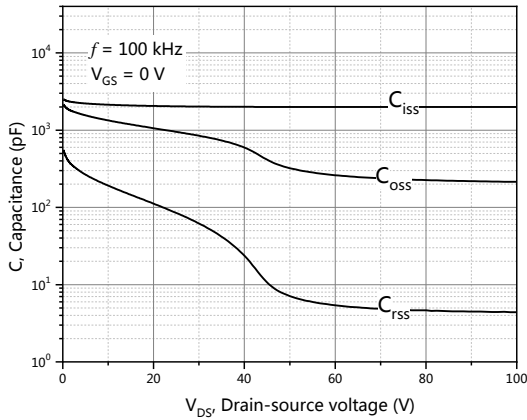


Figure 3, Typ. capacitances

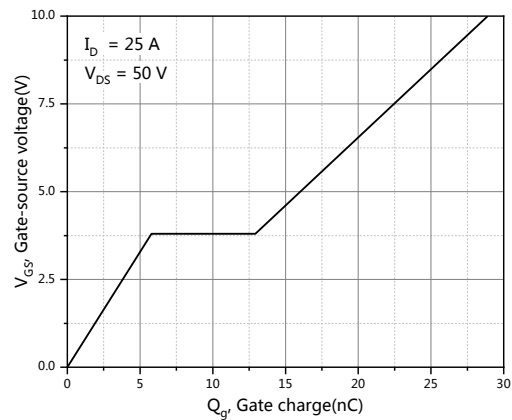


Figure 4, Typ. gate charge

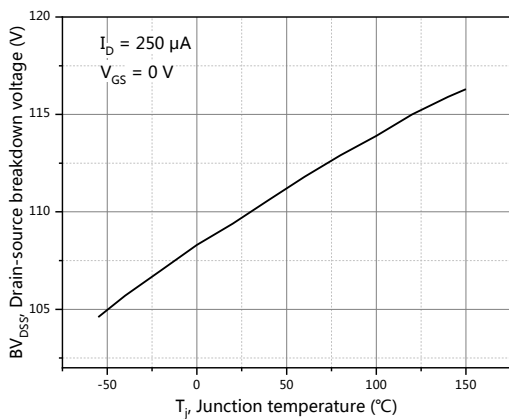


Figure 5, Drain-source breakdown voltage

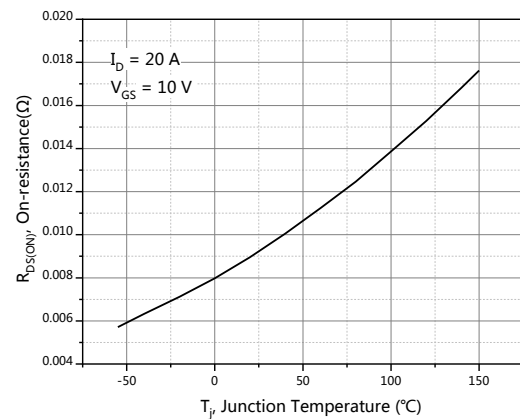


Figure 6, Drain-source on-state resistance

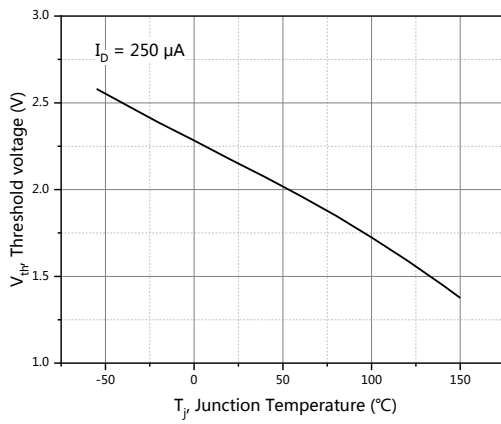


Figure 7, Threshold voltage

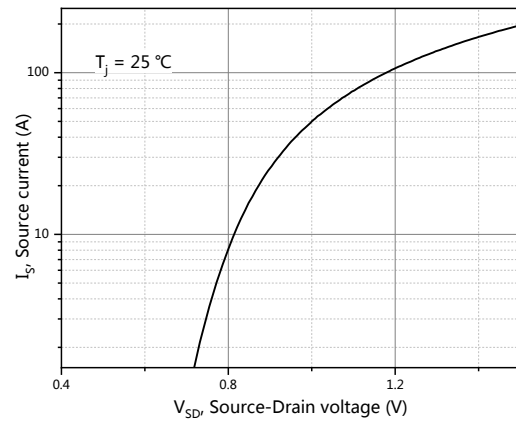


Figure 8, Forward characteristic of body diode

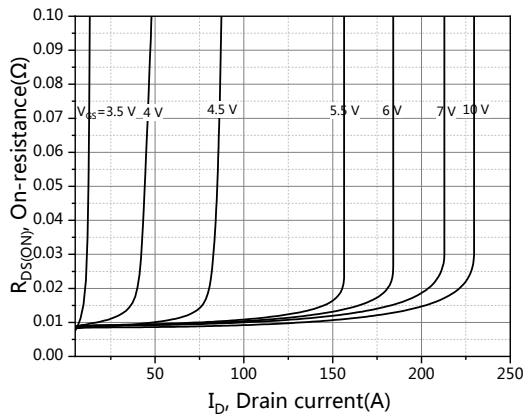


Figure 9, Drain-source on-state resistance

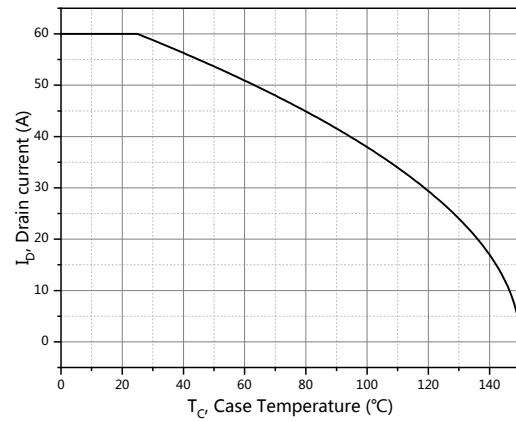


Figure 10, Drain current

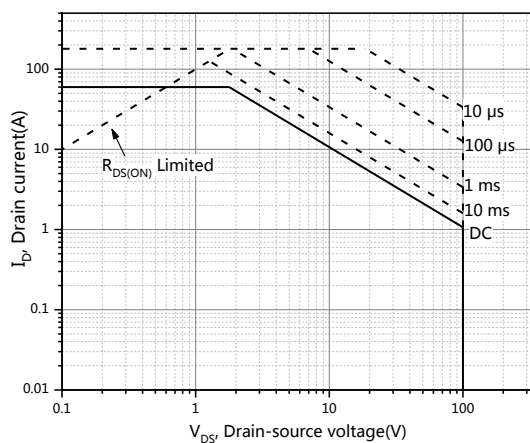


Figure 11, Safe operation area $T_C=25\text{ }^\circ\text{C}$



Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you intend to use.
- 9, this catalog provides information as of Sep. 2014. Specifications and information herein are subject to change without notice.